

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

# 2SK881

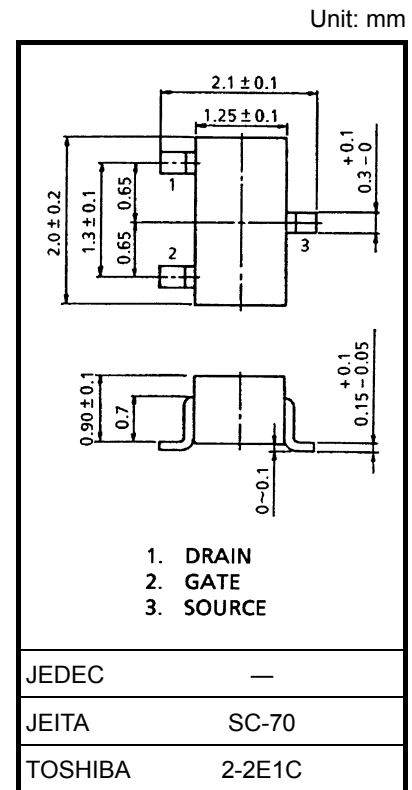
FM Tuner Applications  
VHF Band Amplifier Applications

- Low noise figure:  $NF = 2.5\text{dB}$  (typ.) ( $f = 100\text{ MHz}$ )
- High forward transfer admittance:  $|Y_{fs}| = 9\text{ mS}$  (typ.)

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	$V_{GDO}$	-18	V
Gate current	$I_G$	10	mA
Drain power dissipation	$P_D$	100	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~125	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

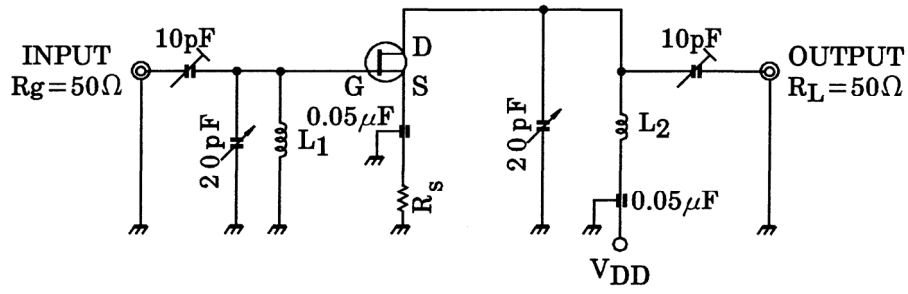


Weight: 0.006 g (typ.)

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = -0.5\text{ V}, V_{DS} = 0$	—	—	-10	nA
Gate-drain breakdown voltage	$V_{(BR)GDO}$	$I_G = -10\ \mu\text{A}$	-18	—	—	V
Drain current	$I_{DSS}$ (Note)	$V_{GS} = 0, V_{DS} = 10\text{ V}$	1.0	—	10	mA
Gate-source cut-off voltage	$V_{GS(OFF)}$	$V_{DS} = 10\text{ V}, I_D = 1\ \mu\text{A}$	-0.4	—	-4.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{GS} = 0, V_{DS} = 10\text{ V}, f = 1\text{ kHz}$	—	9	—	mS
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	6.0	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	—	0.15	pF
Power gain	$G_{ps}$	$V_{DD} = 10\text{ V}, f = 100\text{ MHz}$ (Figure 1)	10	18	—	dB
Noise figure	NF	$V_{DD} = 10\text{ V}, f = 100\text{ MHz}$ (Figure 1)	—	2.5	3.5	dB

Note:  $I_{DSS}$  classification O: 1.0~3.0, Y: 2.5~6.0, GR: 5.0~10.0



L1: 0.8 mmφ Ag plated Cu wire, 3 turns, 10 mm ID, 10 mm length.

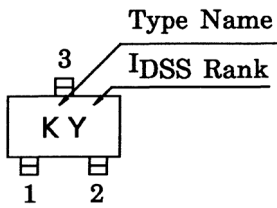
L2: 0.8 mmφ Ag plated Cu wire, 3.5 turns, 10 mm ID, 10 mm length.

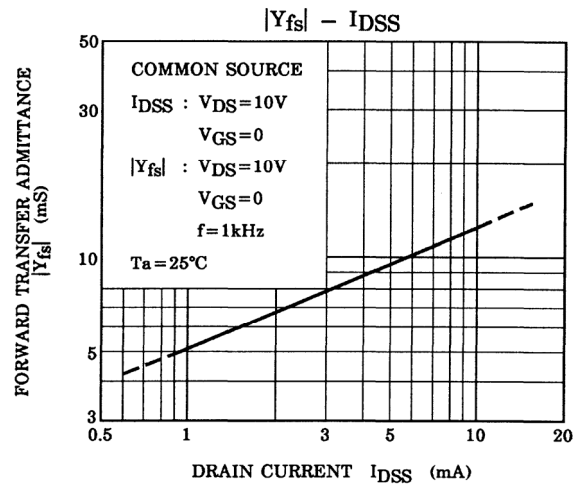
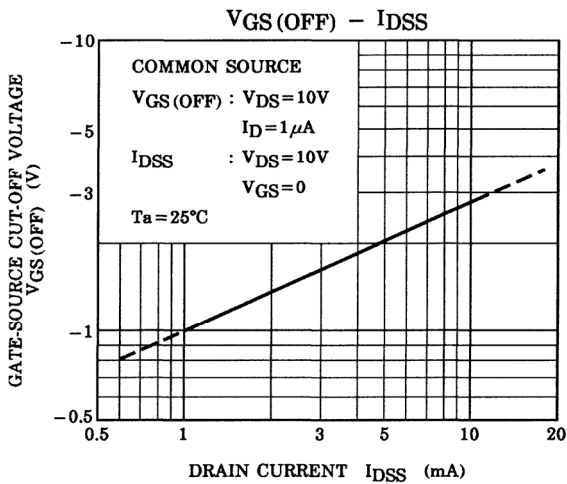
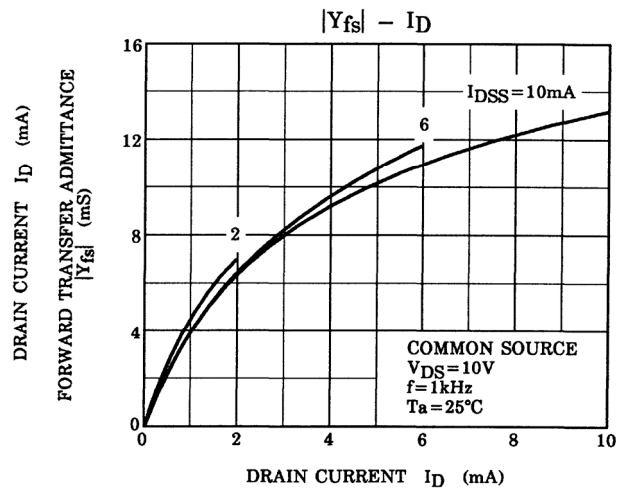
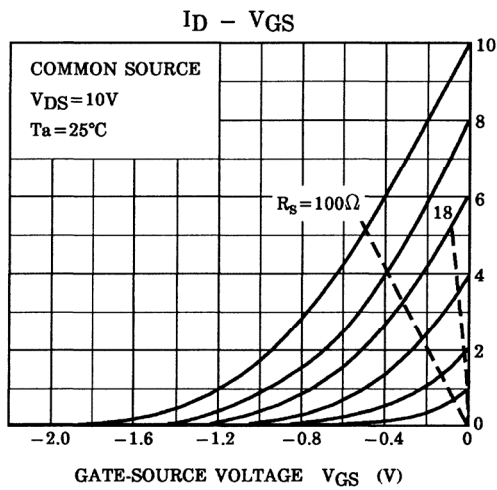
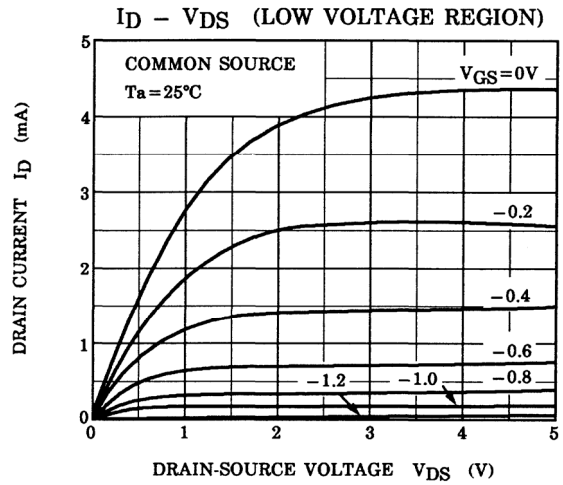
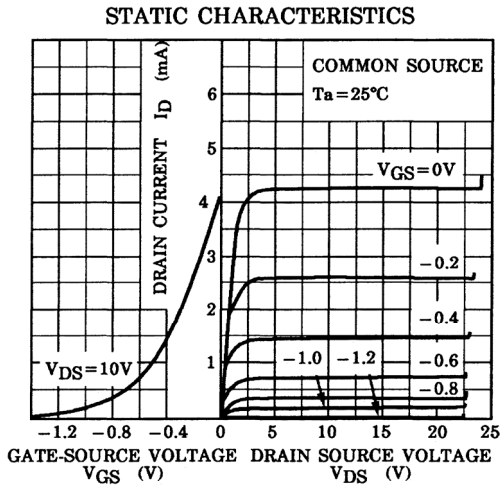
**Figure 1 100 MHz Gps, NF Test Circuit**

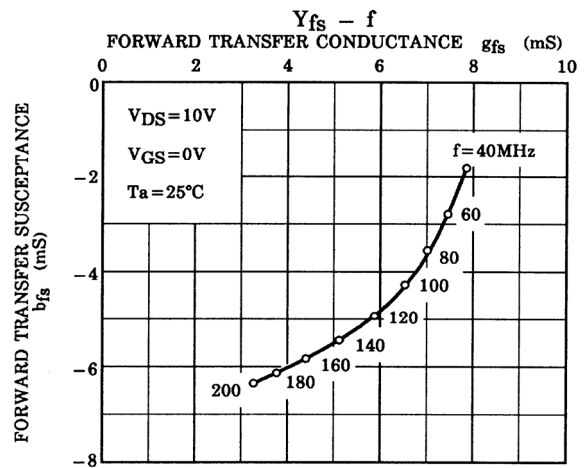
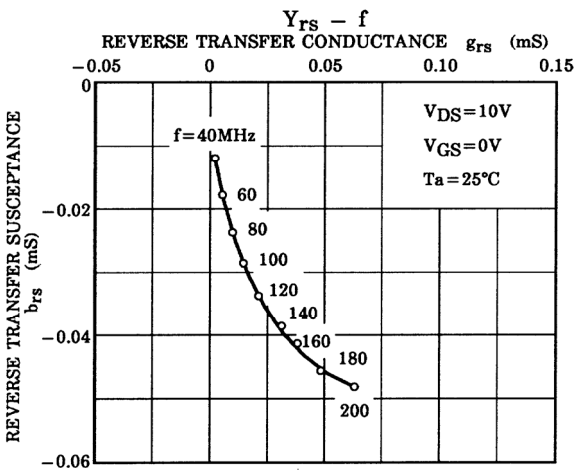
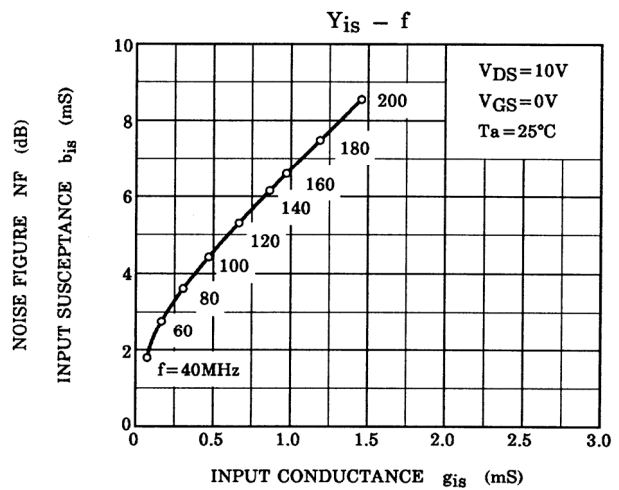
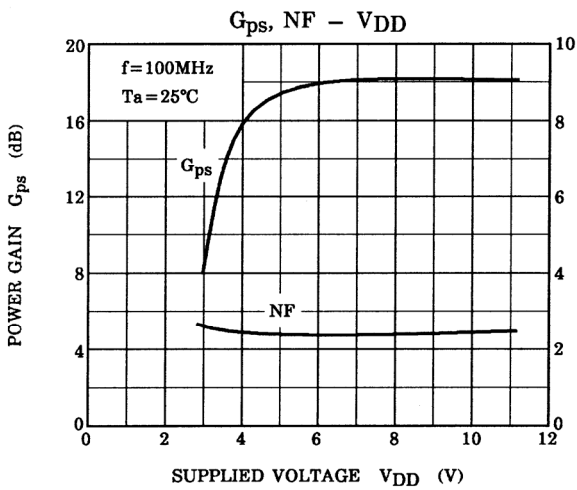
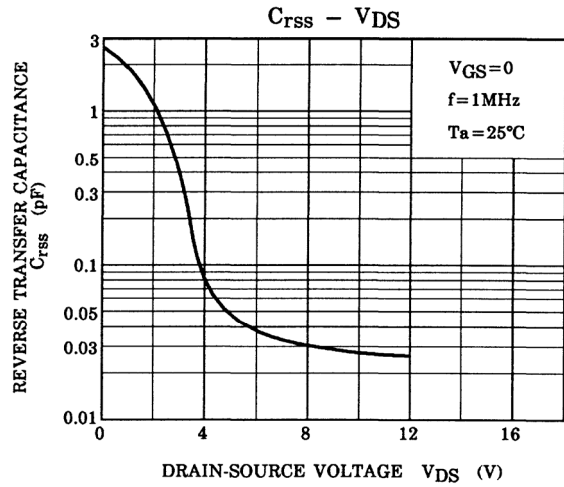
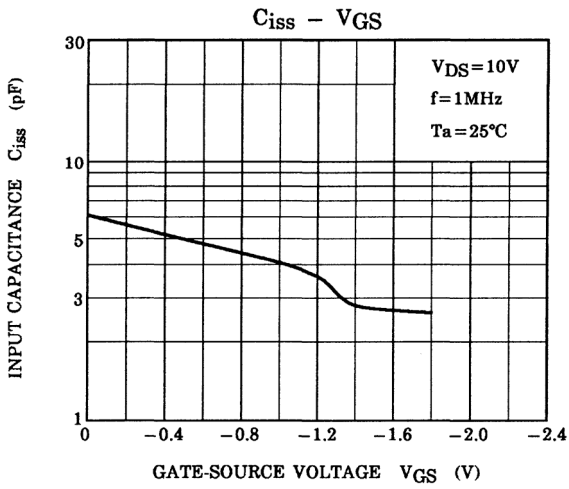
2SK881 is measured at each group by changing  $R_s$ .

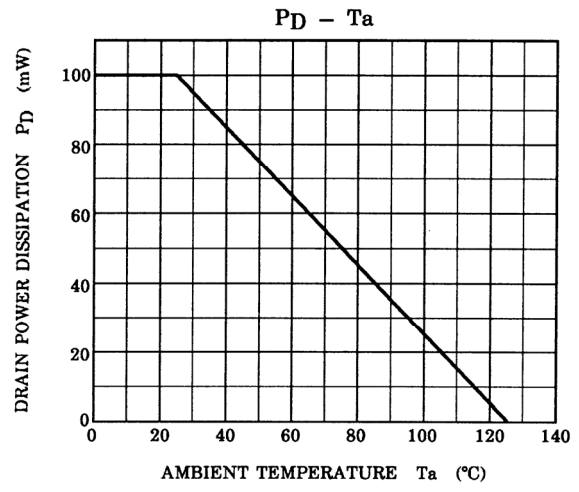
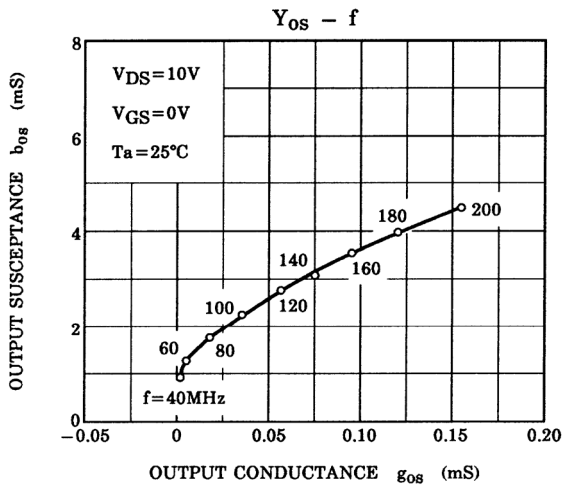
Group	$R_s$ ( $\Omega$ )
2SK881-O	0
2SK881-Y	$18 \Omega \pm 5\%$
2SK881-GR	$100 \Omega \pm 5\%$

**Marking**









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20070701-EN GENERAL

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